

Silicon PNP epitaxial planer type

Complementary to 2SC5026

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- High collector to emitter voltage V_{CEO} .
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-80	V
Collector to emitter voltage	V_{CEO}	-80	V
Emitter to base voltage	V_{EBO}	-5	V
Peak collector current	I_{CP}	-1.5	A
Collector current	I_C	-1	A
Collector power dissipation ($T_C=25^\circ\text{C}$)	P_C^*	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$

Unit: mm

Top View Dimensions:

- Overall width: 4.5 ± 0.1
- Base width: 1.6 ± 0.2
- Base height: 2.6 ± 0.1
- Base angle: 45°
- Base thickness: 0.4 ± 0.08
- Collector thickness: 0.5 ± 0.08
- Emitter thickness: 1.5 ± 0.1
- Base to collector distance: 3.0 ± 0.15
- Collector to emitter distance: 1.0 ± 0.2
- Collector thickness: $+0.1$
- Emitter thickness: $+0.25$
- Collector to emitter distance: 4.0 ± 0.20

Side View Dimensions:

- Base width: 1.5 ± 0.1
- Base height: 2.5 ± 0.1
- Base thickness: 0.4 ± 0.04

Bottom View:

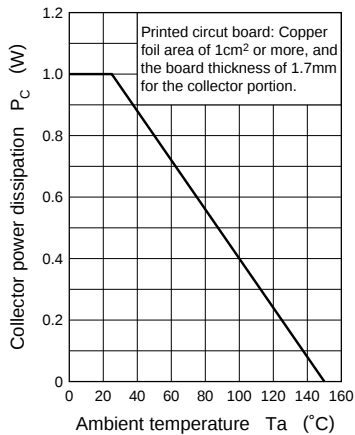
- Marking: 3, 2, 1
- Marking: marking

Marking symbol : 1Z

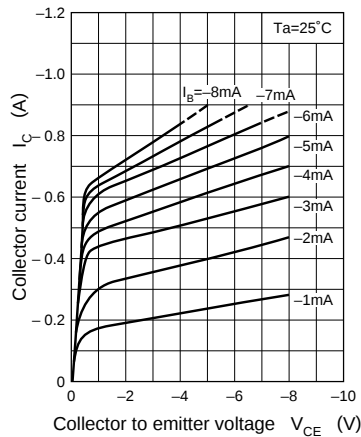
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = -40V, I_E = 0$			-0.1	μA
Collector to base voltage	V_{CBO}	$I_C = -10\mu A, I_E = 0$	-80			V
Collector to emitter voltage	V_{CEO}	$I_C = -1mA, I_B = 0$	-80			V
Emitter to base voltage	V_{EBO}	$I_E = -10\mu A, I_C = 0$	-5			V
Forward current transfer ratio	h_{FE1}^{*1}	$V_{CE} = -2V, I_C = -100mA$	120		340	
	h_{FE2}	$V_{CE} = -2V, I_C = -500mA^{*2}$	60			
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -500mA, I_B = -50mA^{*2}$		-0.2	-0.3	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -500mA, I_B = -50mA^{*2}$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10V, I_E = 50mA, f = 200MHz$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$		15	30	pF

Rank	Q	R
h_{FE1}	120 ~ 240	170 ~ 340

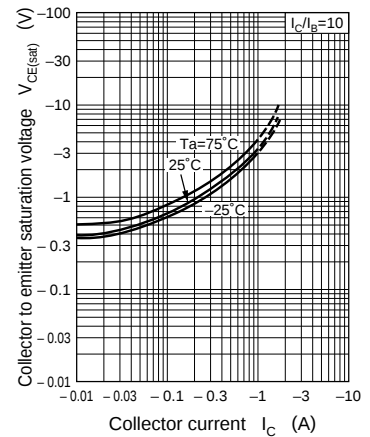
$P_C - T_a$



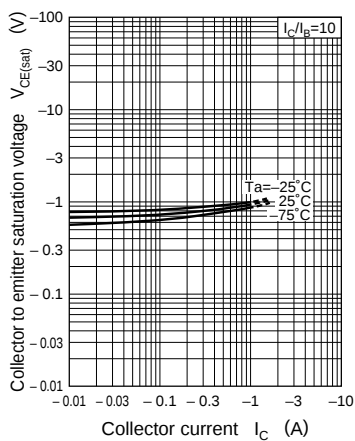
$I_C - V_{CE}$



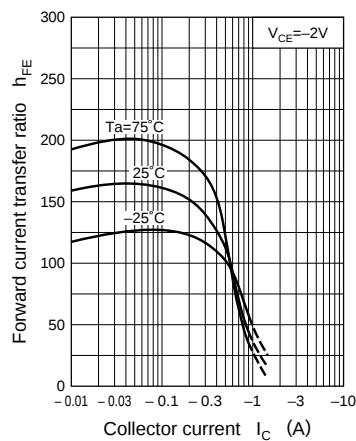
$V_{CE(\text{sat})} - I_C$



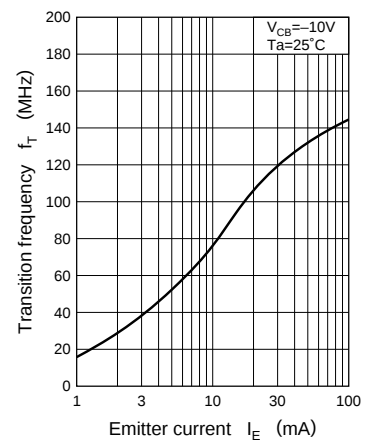
$V_{BE(\text{sat})} - I_C$



$h_{FE} - I_C$



$f_T - I_E$



$C_{ob} - V_{CB}$

